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**April 2014** 

#### SSU1N50B

#### 520V N-Channel MOSFET

#### **General Description**

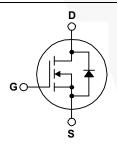
These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switch mode power supplies, power factor correction and electronic lamp ballasts based on half bridge.

#### **Features**

- 1.3A, 520V,  $R_{DS(on)} = 5.3\Omega$  @  $V_{GS} = 10$  V Low Gate Charge (Typ. 8.3 nC)
- Low Crss (Typ. 5.5 pF)
- Fast Switching
- 100% Avalanche Tested
- · Improved dv/dt Capability





#### Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Parameter		SSU1N50BTU	Unit
V <sub>DSS</sub>	Drain-Source Voltage		520	V
I <sub>D</sub>	Drain Current - Continuous (T <sub>C</sub> = 25°	C)	1.3	Α
	- Continuous (T <sub>C</sub> = 100	0°C)	0.82	Α
I <sub>DM</sub>	Drain Current - Pulsed	(Note 1)	5.0	Α
V <sub>GSS</sub>	Gate-Source Voltage		± 30	V
E <sub>AS</sub>	Single Pulsed Avalanche Energy	(Note 2)	100	mJ
I <sub>AR</sub>	Avalanche Current	(Note 1)	1.3	А
E <sub>AR</sub>	Repetitive Avalanche Energy	(Note 1)	2.6	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)		5.5	V/ns
P <sub>D</sub>	Power Dissipation (T <sub>A</sub> = 25°C) *		2.5	W
	Power Dissipation (T <sub>C</sub> = 25°C)		26	W
	- Derate above 25°C		0.21	W/°C
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Temperature Range		-55 to +150	°C
T <sub>L</sub>	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		300	°C

#### **Thermal Characteristics**

Symbol	Parameter	SSU1N50BTU	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	4.76	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (*1 in² Pad of 2-oz Copper), Max	50	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Minimum Pad of 2-oz Copper), Max.	110	°C/W

## **Package Marking and Ordering Information**

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
SSU1N50BTU	SSU1N50B	I-PAK	Tube	N/A	N/A	70 units

Symbol	Parameter	Test Conditions	Min	Тур	Max	Uni
Off Cha	aracteristics					
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = 250 \mu\text{A}$	520			V
$\Delta BV_{DSS}$ / $\Delta T_{J}$	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250 μA, Referenced to 25°C		0.54		V/°C
I <sub>DSS</sub>	Zero Cata Valla va Brain Command	V <sub>DS</sub> = 520 V, V <sub>GS</sub> = 0 V			10	μΑ
	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 400 V, T <sub>C</sub> = 125°C			100	μΑ
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 30 V, V <sub>DS</sub> = 0 V			100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = -30 V, V <sub>DS</sub> = 0 V		-	-100	nA
On Cha	aracteristics					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	2.0		4.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 0.65 A		4.1	5.3	Ω
9 <sub>FS</sub>	Forward Transconductance	$V_{DS} = 40 \text{ V}, I_{D} = 0.65 \text{ A}$		1.65		S
C <sub>iss</sub>	ic Characteristics Input Capacitance	V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V,		260	340	pF
C <sub>oss</sub>	Output Capacitance	$v_{DS} = 25 \text{ v}, v_{GS} = 0 \text{ v},$ $f = 1.0 \text{ MHz}$		25	33	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			5.5	7.2	pF
Switchi	ing Characteristics					
t <sub>d(on)</sub>	Turn-On Delay Time			14	40	ns
t <sub>r</sub>	Turn-On Rise Time	$V_{DD} = 250 \text{ V}, I_{D} = 1.5 \text{ A},$		40	90	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	$R_G = 25 \Omega$		35	80	ns
t <sub>f</sub>	Turn-Off Fall Time	(Note 4)		35	80	ns
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> = 400 V, I <sub>D</sub> = 1.5 A,	/	8.3	11	nC
Q <sub>gs</sub>	Gate-Source Charge	$V_{GS} = 10 \text{ V}$		1.5		nC
Q <sub>gd</sub>	Gate-Drain Charge	(Note 4)		3.4		nC
	Source Diede Characteristics as	nd Maximum Patings				
Drain-Source Diode Characteristics and Maximum Ratings  Maximum Continuous Drain-Source Diode Forward Current					1.3	Α
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward Current			-	5.0	A
UIVI		V <sub>GS</sub> = 0 V, I <sub>S</sub> = 1.3 A		-	1.4	V
V <sub>SD</sub>	Diain-Source Dioge Forward vollage					
V <sub>SD</sub>	Drain-Source Diode Forward Voltage Reverse Recovery Time	$V_{GS} = 0 \text{ V}, I_S = 1.5 \text{ A},$		230		ns

**Notes:** 1. Repetitive Rating : Pulse width limited by maximum junction temperature. 2. L = 106mH,  $I_{AS}$  = 1.5A,  $V_{DD}$  = 50V,  $R_G$  = 25  $\Omega$ , Starting  $T_J$  = 25°C. 3.  $I_{SD} \le$  1.5A,  $di/dt \le$  300A/ $\mu$ s,  $V_{DD} \le$  BV $_{DSS}$ , Starting  $T_J$  = 25°C. 4. Essentially independent of operating temperature.

#### **Typical Characteristics**

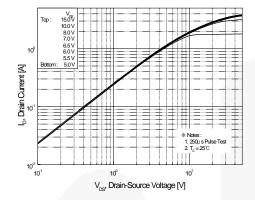


Figure 1. On-Region Characteristics

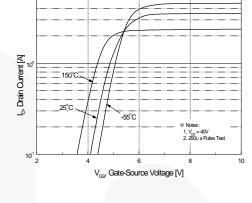


Figure 2. Transfer Characteristics

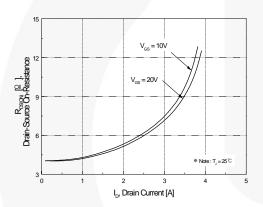


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

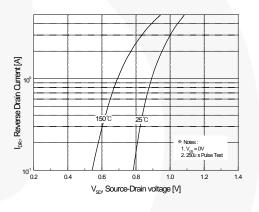


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

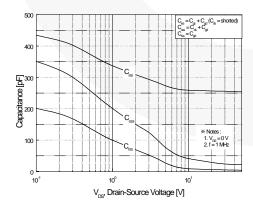


Figure 5. Capacitance Characteristics

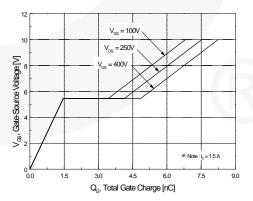


Figure 6. Gate Charge Characteristics

# BV<sub>rss</sub>, (Nomalized) Drain-Source Breakdown Vdtage -100

Typical Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs Temperature

 $T_{_J}$ , Junction Temperature [°C]

150

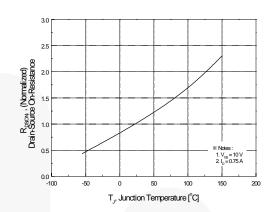


Figure 8. On-Resistance Variation vs Temperature

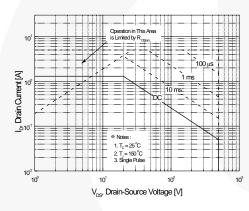


Figure 9. Maximum Safe Operating Area

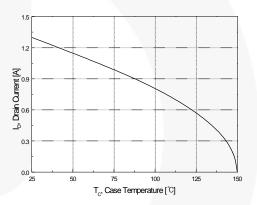


Figure 10. Maximum Drain Current vs Case Temperature

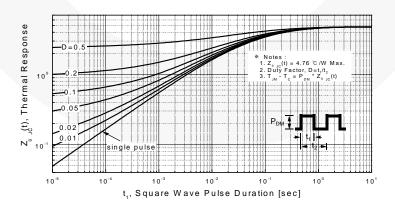


Figure 11. Transient Thermal Response Curve



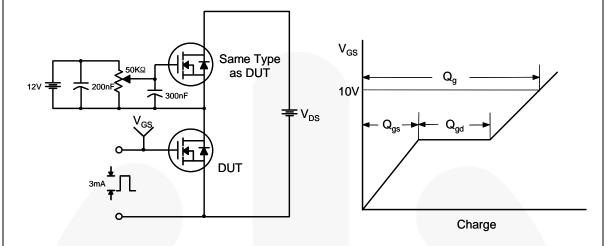


Figure 13. Resistive Switching Test Circuit & Waveforms

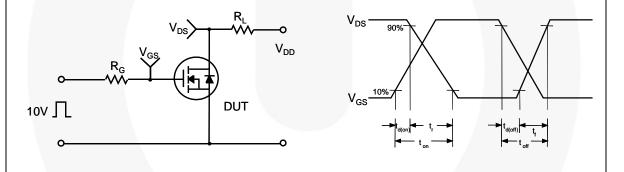
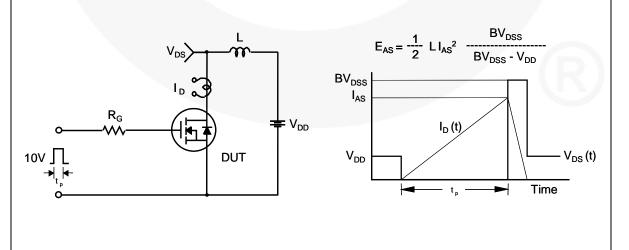
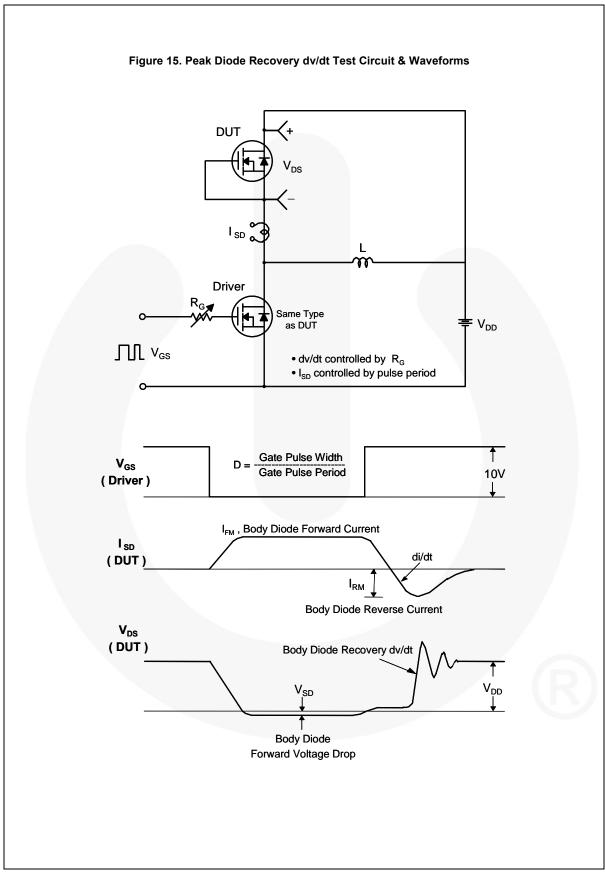


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms





#### **Mechanical Dimensions**

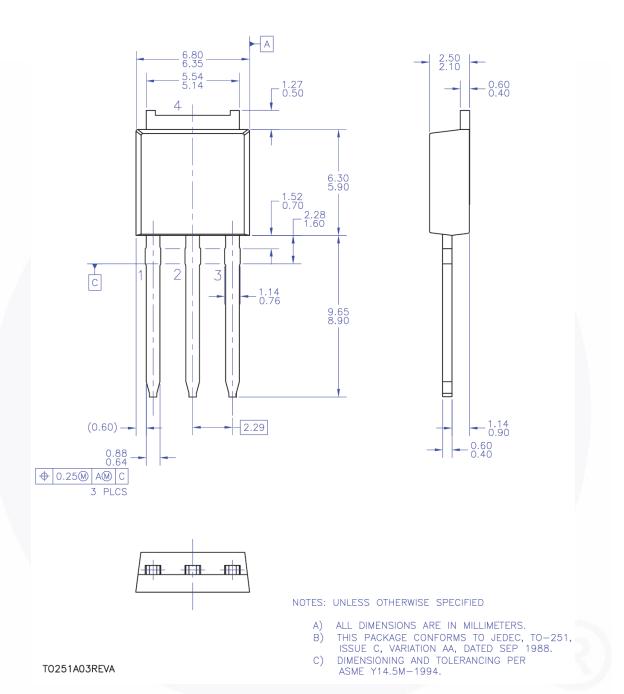


Figure 16. TO251 (I-PAK), Molded, 3-Lead

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